

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

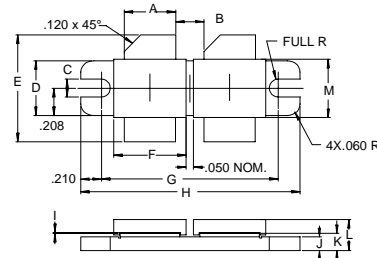
The **ASI SD1492** is a Common Emitter Device Designed for Class AB operation in UHF Amplifier Applications in Television Band IV & V Transmitters.

**FEATURES INCLUDE:**

- Gold Metalization
- Emitter Ballasting
- Internal Matching

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	25 A
<b>V<sub>CB0</sub></b>	60 V
<b>P<sub>DISS</sub></b>	310 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	0.55 °C/W

**PACKAGE STYLE .450 BAL FLG.(A)**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.373 / 9.47	.385 / 9.78
B	.205 / 5.21	
C	.120 / 3.25	.130 / 3.30
D	.411 / 10.44	.421 / 10.69
E	.825 / 20.96	.865 / 21.97
F	.525 / 13.34	.535 / 13.59
G	1.255 / 31.88	1.265 / 32.18
H	1.675 / 42.55	1.685 / 42.80
I	.002 / 0.05	.006 / 0.15
J	.095 / 2.41	.105 / 2.67
K	.115 / 2.92	.135 / 3.43
L	.250 / 6.35	
M	.445 / 11.30	.457 / 11.61

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS (PER SIDE)	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 100 mA	30			<b>V</b>
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 100 mA	60			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 50 mA	3.0			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 28 V			10	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 3.0 A	15		70	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 28 V      f = 1.0 MHz			100	<b>pF</b>
<b>P<sub>OUT</sub></b>	V <sub>CE</sub> = 28 V      I <sub>CQ</sub> = 2 X 500 mA      f = 860 MHz	150			<b>W</b>
<b>G<sub>P</sub></b>	V <sub>CE</sub> = 28 V      I <sub>CQ</sub> = 2 X 250 mA      f = 860 MHz	6.5			<b>dB</b>
<b>n<sub>c</sub></b>	P <sub>out</sub> = 150 W	45			<b>dBc</b>